



ZPT034B-N

Technical Data Sheet

3mm Silicon Phototransistor



Descriptions

ZPT034B- N is a high speed and high sensitive NPN silicon phototransistor molded in a standard 3 mm package.

Due to its black epoxy the device is sensitive to visible and near infrared radiation.

Features

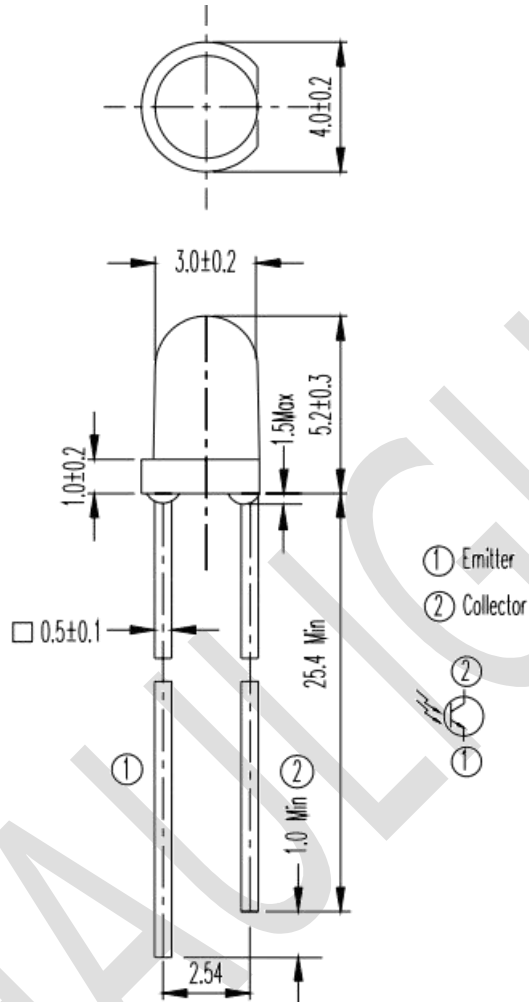
- Fast response times
- High photo sensitivity
- Copliance with EU REACH
- Pb.Free
- The product itself will remain within RoHS compliant version.
- Compliance Halogen Free. (Br<900 ppm, Cl<900ppm, Br+Cl<1500ppm)

Applications

- Camera
- Infrared applied system



Package Dimension



Notes:

- 1.All dimensions are in millimeters
- 2.Tolerances unless dimensions ± 0.3 mm
- 3.Lead spacing is measured where the lead emerge from the package



Absolute Maximum Ratings (Ta=25°C)

Parameter (Ta=25°C)	Symbol	Ratings	Unit
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Collector-Voltage	V _{ECO}	5	V
Collector Current	I _C	20	mA
Operating Temperature	T _{opr}	-40 ~ +85	°C
Storage Temperature	T _{stg}	-40 ~ +100	°C
Lead Soldering Temperature*1	T _{sol}	260	°C
Power Dissipation at (or below)25°C Free Air Temperature	P _c	75	mW

Notes: *1: Soldering time \leq 5 seconds.



Electro-Optical Characteristics

Parameter (Ta=25°C)	Symbol	Condition	Min.	Typ.	Max.	Unit
Collector – Emitter Breakdown Voltage	BV_{CEO}	$I_C=100\ \mu A$ $E_e=0mW/cm^2$	30	--	--	V
Emitter-Collector Breakdown Voltage	BV_{ECO}	$I_E=100\ \mu A$ $E_e=0mW/cm^2$	5	--	--	V
Collector-Emitter Saturation Voltage	$V_{CE}(sat)$	$I_C=2mA$ $E_e=1mW/cm^2$	--	--	0.4	V
Rise Time	t_r	$V_{CE}=5V$	--	15	--	μS
Fall Time	t_f	$I_C=1mA$ $R_L=1000\Omega$	--	15	--	
Collector Dark Current	I_{CEO}	$E_e=0mW/cm^2$ $V_{CE}=20V$	--	--	100	nA
On State Collector Current	$I_C(on)$	$E_e=1mW/cm^2$ $V_{CE}=5V$	1.77	3.15	5.07	mA
Wavelength of Peak Sensitivity	λ_p	--	--	940	--	nm
Rang of Spectral Bandwidth	$\lambda_{0.5}$	--	840	--	1100	nm

Note:

Tolerance of Luminous Intensity: $\pm 10\%$

Tolerance of Dominant Wavelength: $\pm 1nm$

Tolerance of Forward Voltage: $\pm 0.1V$



Rank

Parameter	Symbol	Condition	Min.	Max.	Unit
J	$I_{C(ON)}$	VCE=5V Ee=1mW/c m ²	1.77	3.61	mA
K	$I_{C(ON)}$	VCE=5V Ee=1mW/c m ²	2.67	5.07	mA

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Typical Electro-Optical Characteristics Curves

Fig.1 Collector Power Dissipation vs. Ambient Temperature

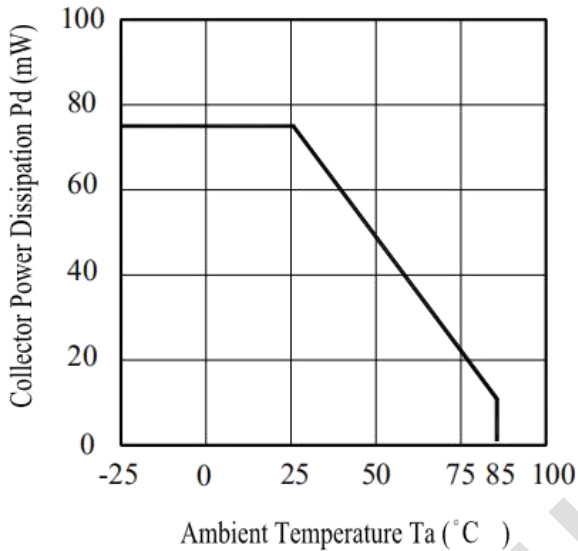


Fig.2 Spectral Sensitivity

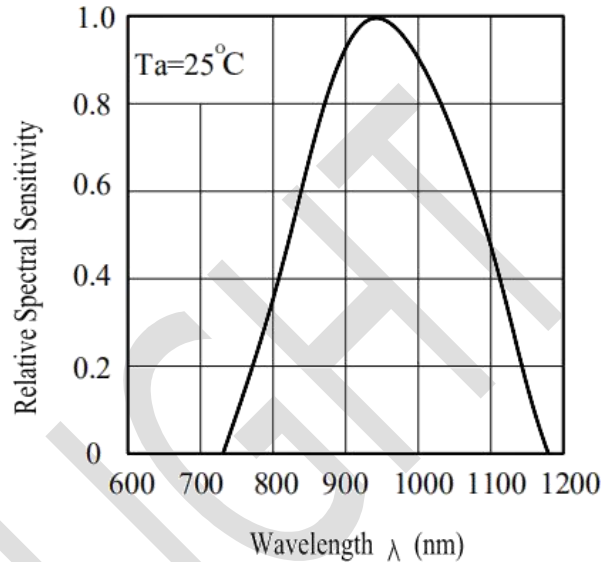


Fig.3 Relative Collector Current vs. Ambient Temperature

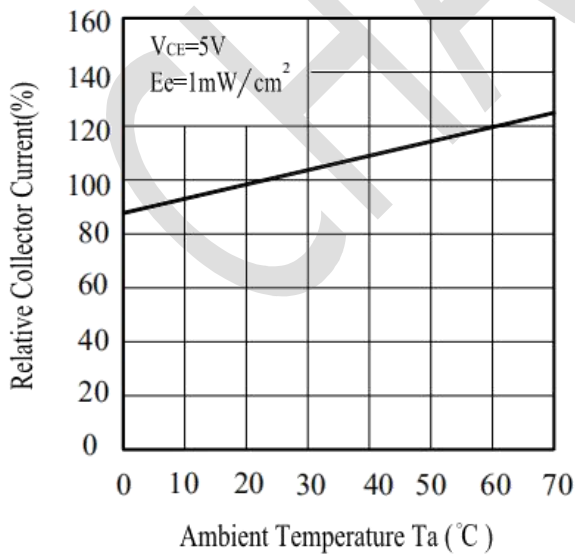


Fig.4 Collector Current vs. Irradiance

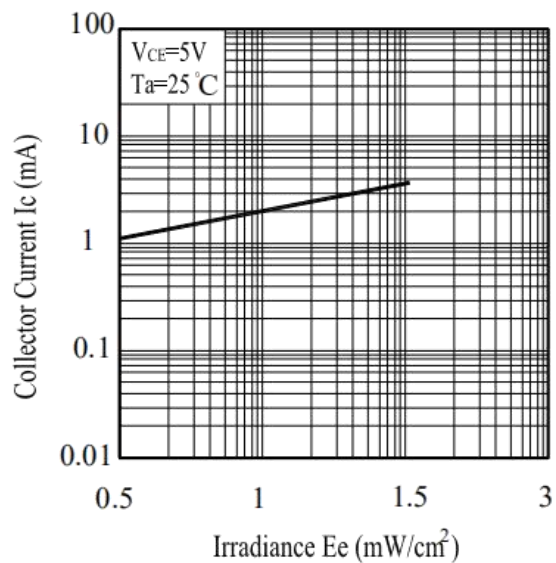




Fig.5 Collector Dark Current vs. Ambient Temperature

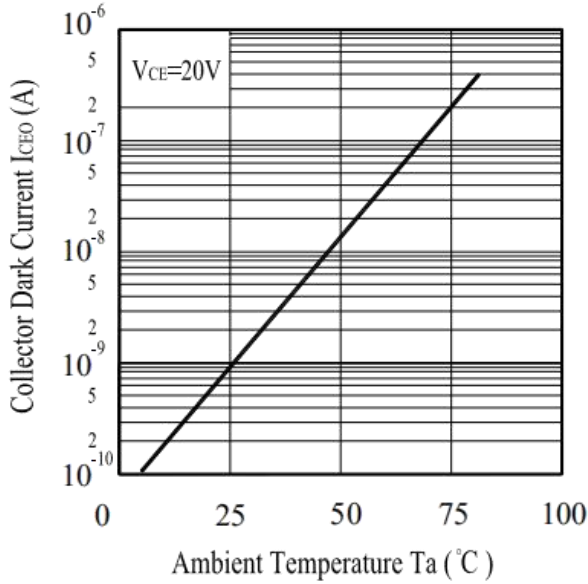
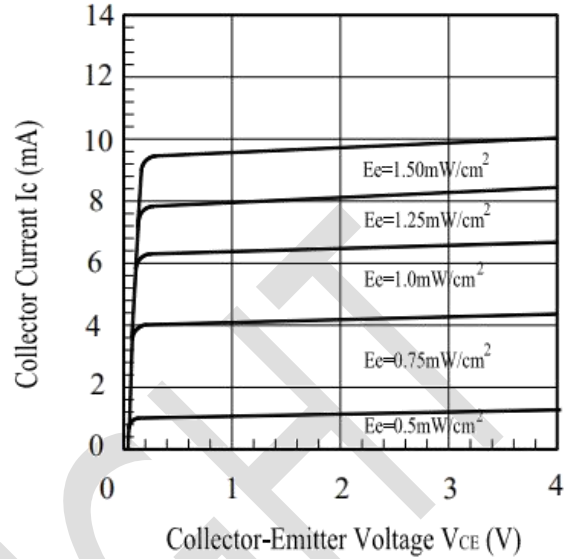


Fig.6 Collector Current vs. Collector-Emitter Voltage





Packing Quantity Specification

1. 1000PCS/1bag, 4bags/1 Box
2. 10BOXES/1 Carton

Notes

1. Above specification may be changed without notice. CHAU LIGHT will reserve authority on material change for above specification.
2. When using this product, please observe the absolute maximum ratings and the instruction for using outlined in these specification sheets. CHAU LIGHT assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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